

## IN THE UNFIED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al. Examiner: Son T. Dinh

Serial No.: 09/945,507 Group Art Unit: 2824

Filed: August 30, 2001 Docket: 1303.014US1

Title: FLASH MEMORY WITH LOW TUNNEL BARRIER INTERPOLY

**INSULATORS** 

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS RCE Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Supplemental Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Supplemental Information Disclosure Statement considered.

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The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. P.O. Box 2938
Minneapolis, MN 55402
(612) 349-9587

25 H/16

Timothy B Clise

Reg. No. 40,957

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this day of September, 2005.

Nama

Signature Loo

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on of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE 09/945,507 **Application Number** STATEMENT BY APPLICANT August 30, 2001 (Use as many sheets as necessary) **Filing Date First Named Inventor** Forbes, Leonard SEP 06 2005 2824 **Group Art Unit Examiner Name** Dinh, Son Attorney Docket No: 1303.014US1 Sheet 1 of 2

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**EXAMINER** 

**DATE CONSIDERED** 

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(Use as many sheets as necessary)	Filing Date	August 30, 2001	
	First Named Inventor	Forbes, Leonard	
	Group Art Unit	2824	
	Examiner Name	Dinh, Son	
Sheet 2 of 2	Attorney Docket No: 1303.014US1		

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